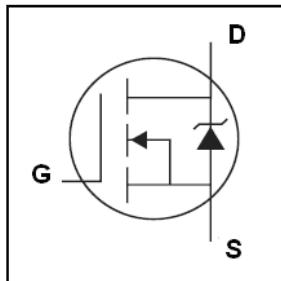


## Features

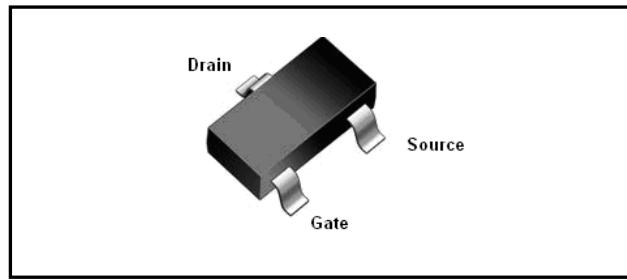
- ◆ Low On-Resistance
- ◆ Fast Switching
- ◆ High Effective
- ◆ Lead-Free, RoHS Compliant



$V_{DSS}$	60V
$R_{DS(on)}$	95mΩ
$I_D$	3A

## Description

SL03N06 designed by the trench processing techniques to achieve extremely low on-resistance. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Switch applications and a wide variety of other small power supply applications.



## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Rating	Unit
<b>Common Ratings (T<sub>c</sub>=25°C Unless Otherwise Noted)</b>			
V <sub>GS</sub>	Gate-Source Voltage	±20	V
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	60	V
T <sub>J</sub>	Maximum Junction Temperature	175	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 155	°C
I <sub>S</sub>	Diode Continuous Forward Current	T <sub>c</sub> =25°C 3	A
<b>Mounted on Large Heat Sink</b>			
I <sub>DM</sub>	Pulse Drain Current Tested ①	T <sub>c</sub> =25°C 12	A
I <sub>D</sub>	Continuous Drain current@V <sub>GS</sub> =4.5V ②	T <sub>c</sub> =25°C 3	A
P <sub>D</sub>	Maximum Power Dissipation	T <sub>c</sub> =25°C 1.75	W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient	155	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	60	--	--	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current( $T_c=25^\circ\text{C}$ )	$V_{\text{DS}}=60\text{V}$ , $V_{\text{GS}}=0\text{V}$	--	--	1	$\mu\text{A}$
	Zero Gate Voltage Drain Current( $T_c=125^\circ\text{C}$ )	$V_{\text{DS}}=60\text{V}$ , $V_{\text{GS}}=0\text{V}$	--	--	100	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	--	--	$\pm 100$	nA
$V_{\text{GS(TH)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_D=250\mu\text{A}$	0.8	1.1	1.5	V
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=4.5\text{V}$ , $I_D=2\text{A}$	--	95	105	$\text{m}\Omega$
$g_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}=15\text{V}$ , $I_D=1.8\text{A}$	3	--	--	S
<b>Dynamic Electrical Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=30\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	--	250	--	pF
$C_{\text{oss}}$	Output Capacitance		--	35	--	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	20	--	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=30\text{V}$ , $I_D=1\text{A}$ , $V_{\text{GS}}=4.5\text{V}$	--	6	--	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	1.2	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	1.3	--	nC
<b>Switching Characteristics</b>						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=30\text{V}$ , $I_D=1\text{A}$ , $R_G=6.8\Omega$ , $V_{\text{GS}}=4.5\text{V}$	--	6	--	nS
$t_r$	Turn-on Rise Time		--	15	--	nS
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	16	--	nS
$t_f$	Turn-Off Fall Time		--	10	--	nS
<b>Source- Drain Diode Characteristics @ <math>T_J = 25^\circ\text{C}</math> (unless otherwise stated)</b>						
$I_{\text{SD}}$	Source-drain current(Body Diode) ②	$T_c=25^\circ\text{C}$	--	--	3	A
$V_{\text{SD}}$	Forward on voltage	$I_{\text{SD}}=3\text{A}$ , $V_{\text{GS}}=0\text{V}$	--	--	1.2	V

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## Typical Characteristics

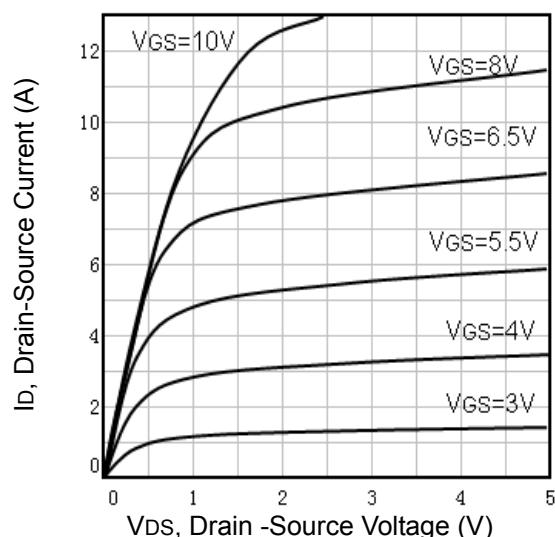


Fig1. Typical Output Characteristics

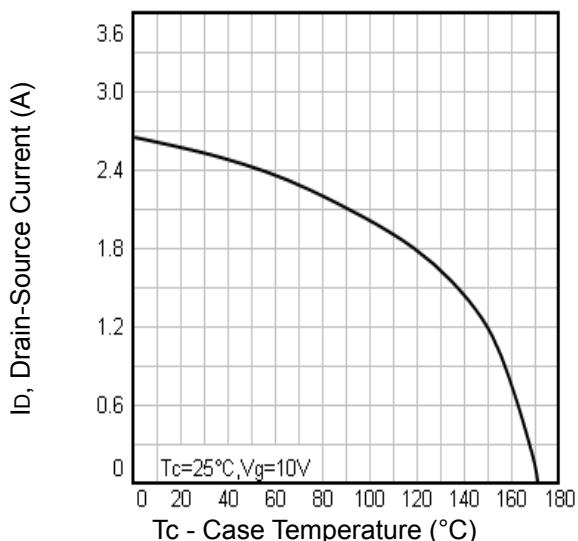


Fig2. Maximum Drain Current Vs. Case Temperature

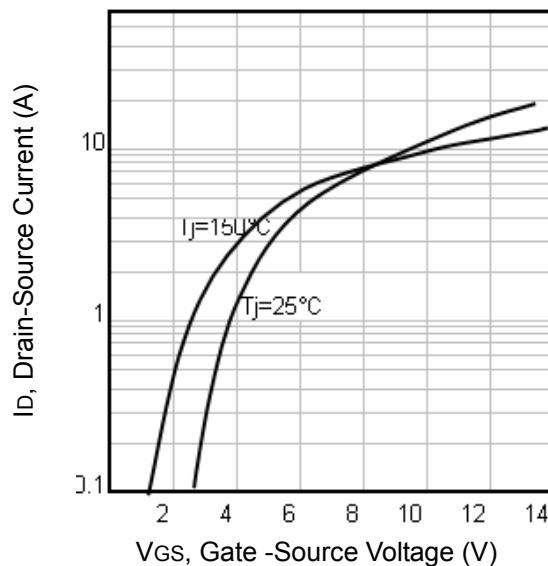


Fig3. Typical Transfer Characteristics

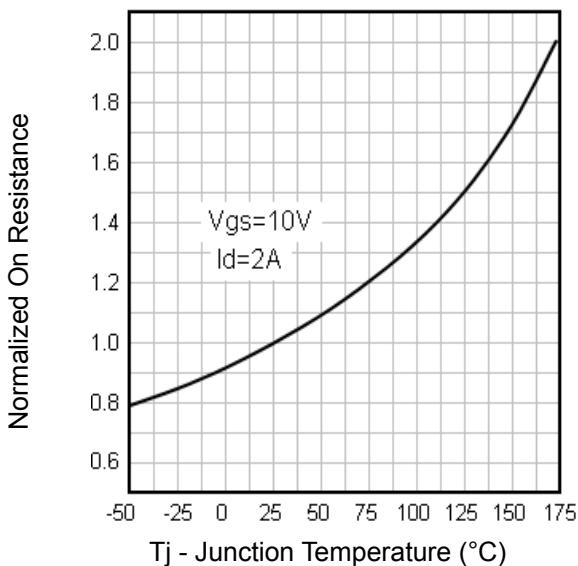


Fig4. Normalized On-Resistance Vs. Temperature

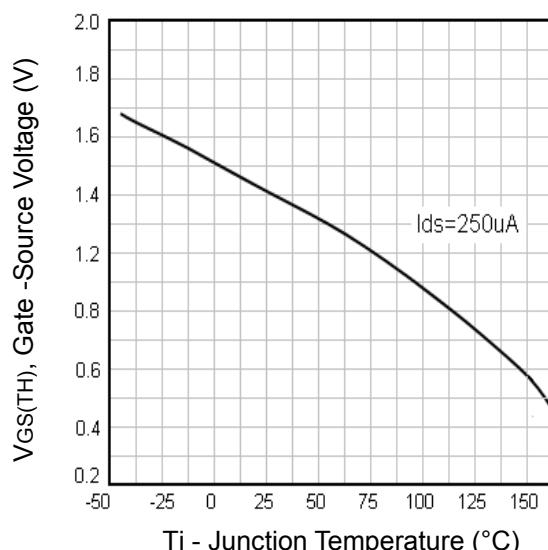


Fig5. Threshold Voltage Vs. Temperature

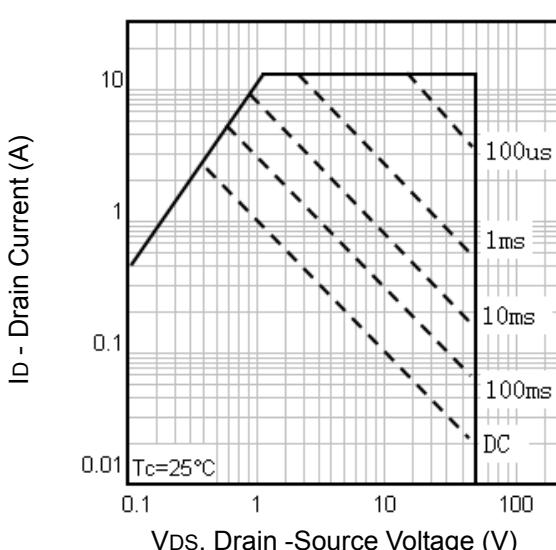
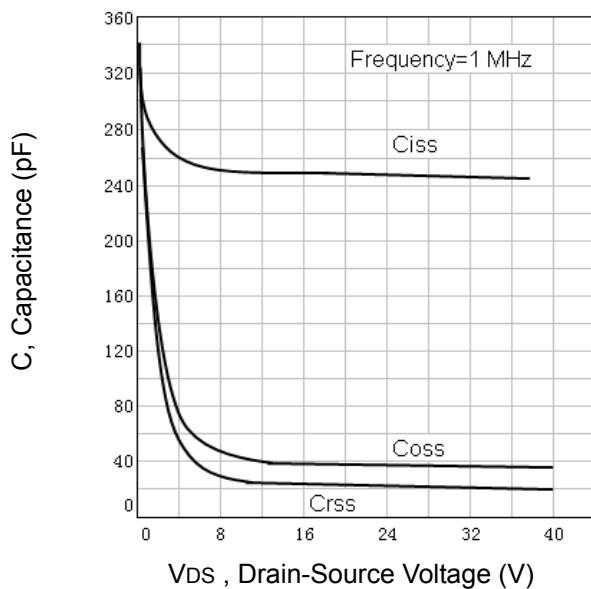
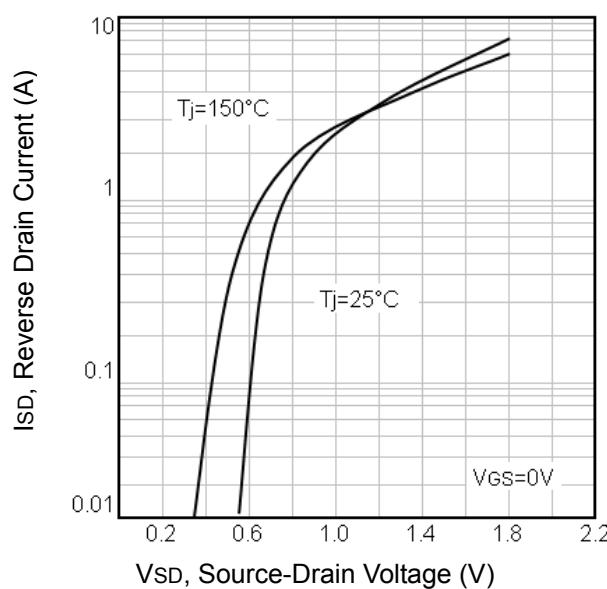
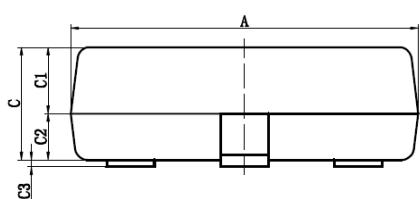
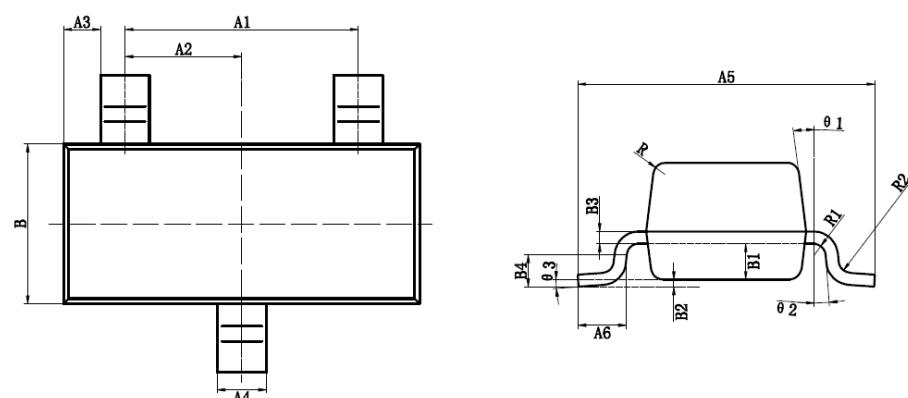


Fig6. Maximum Safe Operating Area



### SOT23 Mechanical Data



尺寸	标注	最小 (mm)	最大 (mm)	尺寸	标注	最小 (mm)	最大 (mm)
A	2.80	3.00		B4		0.254TYP	
A1	1.80	2.00		C		0.975	
A2	0.95TYP			C1		0.585	0.585
A3	0.20	0.40		C2		0.365	0.415
A4	0.30	0.60		C3		0.01	0.11
A5	2.34	2.60		R		0.1TYP	
A6	0.30	0.60		R1		0.1TYP	
B	1.25	1.35		R2		0.1TYP	
B1	0.265	0.315		theta1		6° ~ 8° TYP	
B2	0.01	0.11		theta2		5° REFP	
B3	0.10TYP					1° ~ 7°	

### Order Information

Product	Marking	Package	Packaging	Min Unit Quantity
SL03N06	V36A	SOT23	3000/Reel	6000